AMT1204 6 – 18GHz Low Noise Amplifier Chip



Key Features:

• Frequency range: 6 – 18GHz

Typical gain: 20.5dB (positive slope)Input/output standing wave: 1.6

• Noise figure: 1.6dB

• P-1: 16dBm @ +5V/75mA

• Chip dimensions: 1.40mm x 1.05mm x 0.1mm

• Applications: wireless communication, transceiver module, radio telecommunication etc.

Description:

AMT1204 chip is a Gallium Arsenide (GaAs) high performance Low Noise Amplifier, it covers 6 – 18GHz frequency range. It uses +5V single voltage operation, Noise Figure is 1.6dB, and 20.5dB typical gain. This chip is designed with ground through metal vias on the back technology.

Absolute Maximum Ratings (Ta = 25°C)

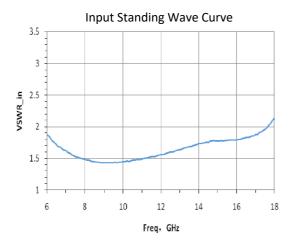
Symbol	Parameter	Value	Remark
Vd	Drain Voltage	7V	
Pin	Input Signal Power	17dBm	
Tch	Operating Temperature	150°C	
Tm	Sintering Temperature	310°C	30s, N2 protection
Tstg	Storage Temperature	-65 ~ +150°C	

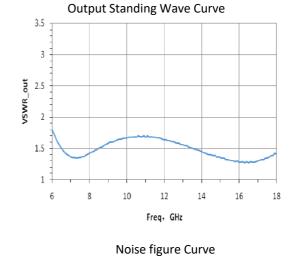
^[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

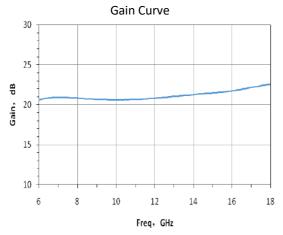
Electrical Characteristics (Ta = 25°C)

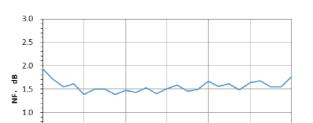
Symbol	Parameter	Test Conditions	Value			Unit
			Min	Typical	Max	
G	Gain		-	20.5	-	dB
NF	Noise Figure		-	1.6	1.9	dB
Id	Static Current	Vd = +5V	-	75	-	mA
VSWR_in	Input Standing Wave	F : 6 ~ 18GHz	-	1.6	2	1
VSWR_out	Output Standing Wave		-	1.6	1.8	1
P-1	Output Power at 1dB point		15	16	-	dBm

Typical Performance









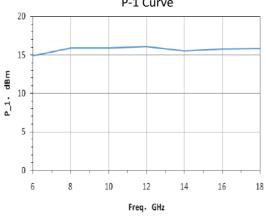
12

Freq, GHz

14

16

18



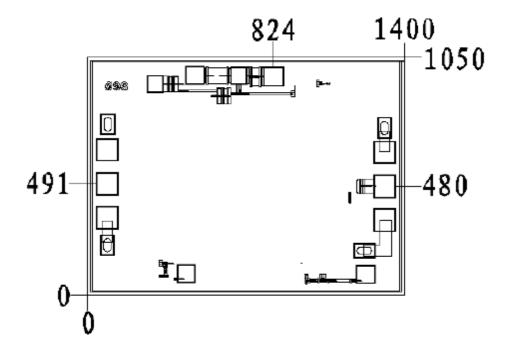
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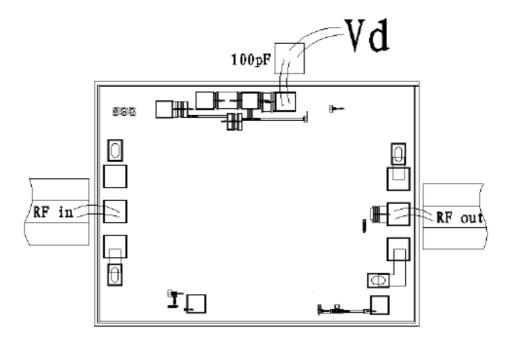
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Chip Dimensions (Unit: µm)



Chip Layout Diagram



Pad Definition

Symbol	Function	Dimension	Equivalent Circuit
RF_in	RF signal input port, connecting to external 50Ω system. no need to add DC blocking capacitor.	100*100μm²	RF-in
RF_out	RF signal output port, connecting to external 50Ω system, no need to add DC blocking capacitor.	100*100μm²	RF_out
Vd	Amplifier bias, need to connect external 100pF capacitor.	100*100μm²	**************************************

Please see Appendix A for details.